- 12 A Continuous On-State Current
- 100 A Surge-Current
- Glass Passivated Wafer
- 400 V to 800 V Off-State Voltage
- Max $I_{GT}$ of 20 mA

**TO-220 PACKAGE**
(TOP VIEW)

Pin 2 is in electrical contact with the mounting base.

---

**absolute maximum ratings over operating case temperature (unless otherwise noted)***

<table>
<thead>
<tr>
<th>RATING</th>
<th>SYMBOL</th>
<th>VALUE</th>
<th>UNIT</th>
</tr>
</thead>
<tbody>
<tr>
<td>Repetitive peak off-state voltage (see Note 1)</td>
<td>$V_{DRM}$</td>
<td>400</td>
<td>V</td>
</tr>
<tr>
<td>Repetitive peak reverse voltage</td>
<td>$V_{RRM}$</td>
<td>400</td>
<td>V</td>
</tr>
<tr>
<td>Continuous on-state current at (or below) 80°C case temperature</td>
<td>$I_{T(RMS)}$</td>
<td>12</td>
<td>A</td>
</tr>
<tr>
<td>Average on-state current (180° conduction angle) at (or below) 80°C case temperature (see Note 3)</td>
<td>$I_{T(AV)}$</td>
<td>7.5</td>
<td>A</td>
</tr>
<tr>
<td>Surge on-state current (see Note 4)</td>
<td>$I_{TM}$</td>
<td>100</td>
<td>A</td>
</tr>
<tr>
<td>Peak positive gate current (pulse width ≤ 300 µs)</td>
<td>$I_{GM}$</td>
<td>3</td>
<td>A</td>
</tr>
<tr>
<td>Peak gate power dissipation (pulse width ≤ 300 µs)</td>
<td>$P_{GM}$</td>
<td>5</td>
<td>W</td>
</tr>
<tr>
<td>Average gate power dissipation (see Note 5)</td>
<td>$P_{G(AV)}$</td>
<td>1</td>
<td>W</td>
</tr>
<tr>
<td>Operating case temperature range</td>
<td>$T_{C}$</td>
<td>-40 to +110</td>
<td>°C</td>
</tr>
<tr>
<td>Storage temperature range</td>
<td>$T_{S}$</td>
<td>-40 to +125</td>
<td>°C</td>
</tr>
<tr>
<td>Lead temperature 1.6 mm from case for 10 seconds</td>
<td>$T_{L}$</td>
<td>230</td>
<td>°C</td>
</tr>
</tbody>
</table>

**NOTES:**
1. These values apply when the gate-cathode resistance $R_{GK} = 1$ kΩ.
2. These values apply for continuous dc operation with resistive load. Above 80°C derate linearly to zero at 110°C.
3. This value may be applied continuously under single phase 50 Hz half-sine-wave operation with resistive load. Above 80°C derate linearly to zero at 110°C.
4. This value applies for one 50 Hz half-sine-wave when the device is operating at (or below) the rated value of peak reverse voltage and on-state current. Surge may be repeated after the device has returned to original thermal equilibrium.
5. This value applies for a maximum averaging time of 20 ms.
### Electrical Characteristics at 25°C Case Temperature

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Test Conditions</th>
<th>MIN</th>
<th>TYP</th>
<th>MAX</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>$I_{DRM}$</td>
<td>Repetitive peak off-state current</td>
<td>$V_D = \text{rated } V_{DRM}$</td>
<td>$R_{GK} = 1 , \text{kΩ}$</td>
<td>$T_C = 110^\circ \text{C}$</td>
<td>2</td>
</tr>
<tr>
<td>$I_{RRM}$</td>
<td>Repetitive peak reverse current</td>
<td>$V_R = \text{rated } V_{RRM}$</td>
<td>$I_G = 0$</td>
<td>$T_C = 110^\circ \text{C}$</td>
<td>2</td>
</tr>
<tr>
<td>$I_G$</td>
<td>Gate trigger current</td>
<td>$V_{AA} = 6 , \text{V}$</td>
<td>$R_L = 100 , \text{Ω}$</td>
<td>$t_{p(g)} \geq 20 , \mu\text{s}$</td>
<td>5</td>
</tr>
<tr>
<td>$V_{GT}$</td>
<td>Gate trigger voltage</td>
<td>$V_{AA} = 6 , \text{V}$</td>
<td>$R_L = 100 , \text{Ω}$</td>
<td>$R_{GK} = 1 , \text{kΩ}$</td>
<td>2.5</td>
</tr>
<tr>
<td>$I_H$</td>
<td>Holding current</td>
<td>$V_{AA} = 6 , \text{V}$</td>
<td>Initiating $I_T = 100 , \text{mA}$</td>
<td>$R_{GK} = 1 , \text{kΩ}$</td>
<td>70</td>
</tr>
<tr>
<td>$V_{TM}$</td>
<td>Peak on-state voltage</td>
<td>$I_{TM} = 12 , \text{A}$</td>
<td>(see Note 6)</td>
<td>$R_{GK} = 1 , \text{kΩ}$</td>
<td>1.4</td>
</tr>
<tr>
<td>$dv/dt$</td>
<td>Critical rate of rise of off-state voltage</td>
<td>$V_D = \text{rated } V_D$</td>
<td>$I_G = 0$</td>
<td>$T_C = 110^\circ \text{C}$</td>
<td>100</td>
</tr>
</tbody>
</table>

**Note 6:** This parameter must be measured using pulse techniques, $t_p = 300 \, \mu\text{s}$, duty cycle $\leq 2\%$. Voltage sensing-contacts, separate from the current carrying contacts, are located within 3.2 mm from the device body.

### Thermal Characteristics

<table>
<thead>
<tr>
<th>Parameter</th>
<th>MIN</th>
<th>TYP</th>
<th>MAX</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>$R_{JUC}$</td>
<td>Junction to case thermal resistance</td>
<td>2.4</td>
<td>°C/W</td>
<td></td>
</tr>
<tr>
<td>$R_{JUA}$</td>
<td>Junction to free air thermal resistance</td>
<td>62.5</td>
<td>°C/W</td>
<td></td>
</tr>
</tbody>
</table>

### Resistive-Load-Switching Characteristics at 25°C Case Temperature

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Test Conditions</th>
<th>MIN</th>
<th>TYP</th>
<th>MAX</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>$t_{gt}$</td>
<td>Gate-controlled turn-on time</td>
<td>$I_T = 5 , \text{A}$</td>
<td>$I_G = 200 , \text{mA}$</td>
<td>See Figure 1</td>
<td>0.8</td>
</tr>
<tr>
<td>$t_q$</td>
<td>Circuit-commutated turn-off time</td>
<td>$I_T = 5 , \text{A}$</td>
<td>$I_{RM} = 10 , \text{A}$</td>
<td>See Figure 2</td>
<td>11</td>
</tr>
</tbody>
</table>
PARAMETER MEASUREMENT INFORMATION

Figure 1. Gate-controlled turn-on time

Figure 2. Circuit-commutated turn-off time

NOTES:
A. Resistor R1 is adjusted for the specified value of $I_{RM}$. 
B. Resistor R2 value is $30/I_H$, where $I_H$ is the holding current value of thyristor TH1. 
C. Thyristor TH1 is the same device type as the DUT. 
D. Pulse Generators, G1 and G2, are synchronised to produce an on-state anode current waveform with the following characteristics: $t_p = 50\,\mu s$ to $300\,\mu s$, duty cycle = 1% 
E. Pulse Generators, G1 and G2, have output pulse amplitude, $V_{G1}$, of $\geq 20\,V$ and duration of 10 $\mu s$ to 20 $\mu s$. 

G2 $t_p$, Synchronisation
TYPICAL CHARACTERISTICS

AVERAGE ON-STATE CURRENT DERATING CURVE

MAX CONTINUOUS ANODE POWER DISSIPATED VS CONTINUOUS ON-STATE CURRENT

SURGE ON-STATE CURRENT VS CYCLES OF CURRENT DURATION

TRANSIENT THERMAL RESISTANCE VS CYCLES OF CURRENT DURATION

---

TIC126 SERIES
SILICON CONTROLLED RECTIFIERS

APRIL 1971 - REVISED MARCH 1997

Figure 3.

Figure 4.

Figure 5.

Figure 6.
TYPICAL CHARACTERISTICS

GATE TRIGGER CURRENT
vs
CASE TEMPERATURE

Figure 7.

GATE TRIGGER VOLTAGE
vs
CASE TEMPERATURE

Figure 8.

GATE FORWARD VOLTAGE
vs
GATE FORWARD CURRENT

Figure 9.

HOLDING CURRENT
vs
CASE TEMPERATURE

Figure 10.
**Typical Characteristics**

**Peak On-State Voltage vs Peak On-State Current**

- $V_{th}$ - Peak On-State Voltage - V
- $I_{th}$ - Peak On-State Current - A

Figure 11.

**Gate-Controlled Turn-On Time vs Gate Current**

- $I_g$ - Gate Current - mA
- $t_{on}$ - Gate-Controlled Turn-On Time - µs

Figure 12.

**Circuit-Commuated Turn-Off Time vs Case Temperature**

- $t_{off}$ - Circuit-Commuated Turn-Off Time - µs
- $T_c$ - Case Temperature - °C

Figure 13.

See Test Circuit and Waveforms
TO-220
3-pin plastic flange-mount package

This single-in-line package consists of a circuit mounted on a lead frame and encapsulated within a plastic compound. The compound will withstand soldering temperature with no deformation, and circuit performance characteristics will remain stable when operated in high humidity conditions. Leads require no additional cleaning or processing when used in soldered assembly.

**NOTES:**
A. The centre pin is in electrical contact with the mounting tab.
B. Mounting tab corner profile according to package version.
C. Typical fixing hole centre stand off height according to package version.
Version 1, 18.0 mm. Version 2, 17.6 mm.
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